

Title (en)
METHOD OF FORMING A CATHODE STRUCTURE

Publication
EP 0068111 B1 19851121 (EN)

Application
EP 82103884 A 19820505

Priority
US 27928181 A 19810630

Abstract (en)
[origin: EP0068111A2] Positive photoresist technology is used on a sapphire substrate (7.1) carrying a patterned metallization layer (11.1) to expose areas (41.3, 41.4) of metallization within delineated apertures in the photoresist. Into these apertures needle-shaped triple carbonate particles (50.3, 50.4) are deposited cataphoretically normal to the metallization areas to form electron emissive areas. A further layer of photoresist is deposited to cover these areas and the first layer of photoresist and exposed through oversize mask so as to leave photoresist as encapsulation material (48.13, 48.14) covering the top and sides of the electron emissive material. The encapsulated planar cathode structure is inserted into a multibeam cathode ray tube and heated so as to remove the encapsulation material.

IPC 1-7
H01J 19/22

IPC 8 full level
H01J 1/13 (2006.01); **H01J 1/16** (2006.01); **H01J 9/04** (2006.01); **H01J 29/04** (2006.01)

CPC (source: EP)
H01J 1/13 (2013.01); **H01J 9/04** (2013.01)

Cited by
EP0755064A3; US5838096A; US11205564B2; US11626273B2

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EP 0068111 A2 19830105; EP 0068111 A3 19830511; EP 0068111 B1 19851121; BR 8203186 A 19830517; DE 3267536 D1 19860102; ES 513515 A0 19830801; ES 518317 A0 19840116; ES 8308153 A1 19830801; ES 8402459 A1 19840116; JP H0363169 B2 19910930; JP S587740 A 19830117; ZA 823101 B 19830330

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